

L293D L293DD

PUSH-PULL FOUR CHANNEL DRIVER WITH DIODES

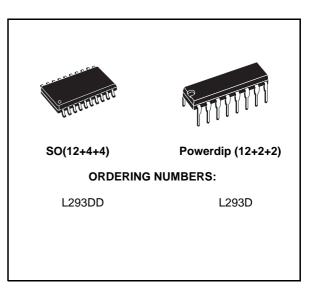
- 600mA OUTPUT CURRENT CAPABILITY PER CHANNEL
- 1.2A PEAK OUTPUT CURRENT (non repetitive) PER CHANNEL
- ENABLE FACILITY
- OVERTEMPERATURE PROTECTION
- LOGICAL "0" INPUT VOLTAGE UP TO 1.5 V (HIGH NOISE IMMUNITY)
- INTERNAL CLAMP DIODES

DESCRIPTION

The Device is a monolithic integrated high voltage, high current four channel driver designed to accept standard DTL or TTL logic levels and drive inductive loads (such as relays solenoides, DC and stepping motors) and switching power transistors.

To simplify use as two bridges each pair of channels is equipped with an enable input. A separate supply input is provided for the logic, allowing operation at a lower voltage and internal clamp diodes are included.

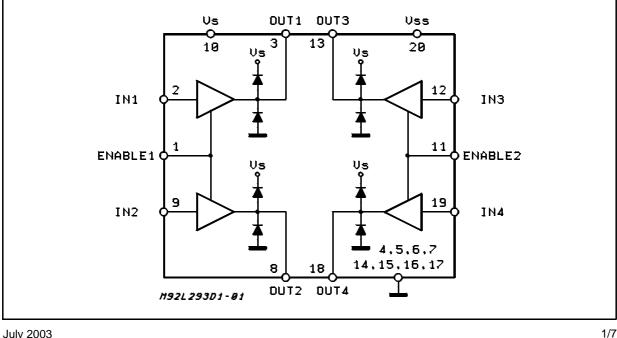
This device is suitable for use in switching applications at frequencies up to 5 kHz.



The L293D is assembled in a 16 lead plastic packaage which has 4 center pins connected together and used for heatsinking

The L293DD is assembled in a 20 lead surface mount which has 8 center pins connected together and used for heatsinking.

BLOCK DIAGRAM



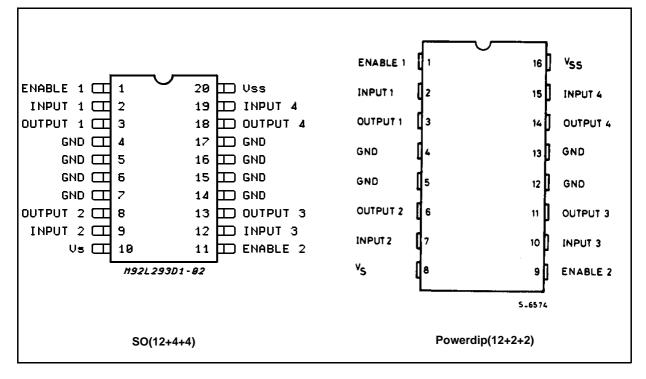
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ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
Vs	Supply Voltage	36	V
Vss	Logic Supply Voltage	36	V
Vi	Input Voltage	7	V
V _{en}	Enable Voltage	7	V
lo	Peak Output Current (100 μs non repetitive)	1.2	А
P _{tot}	Total Power Dissipation at T _{pins} = 90 °C	4	W
T _{stg} , T _j	Storage and Junction Temperature	– 40 to 150	°C

PIN CONNECTIONS (Top view)



THERMAL DATA

Symbol	Decription	DIP	SO	Unit	
R _{th j-pins}	Thermal Resistance Junction-pins	max.	_	14	°C/W
R _{th j-amb}	Thermal Resistance junction-ambient	max.	80	50 (*)	°C/W
R _{th j-case}	Thermal Resistance Junction-case	max.	14	Ι	

(*) With 6sq. cm on board heatsink.



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Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Vs	Supply Voltage (pin 10)		V _{SS}		36	V
V _{SS}	Logic Supply Voltage (pin 20)		4.5		36	V
Is	Total Quiescent Supply Current	$V_i = L \ ; I_O = 0 \ ; V_{en} = H$		2	6	mA
	(pin 10)	$V_i = H \ ; \ I_O = 0 \ ; \ V_{en} = H$		16	24	mA
		V _{en} = L			4	mA
I _{SS}	Total Quiescent Logic Supply	$V_i = L$; $I_O = 0$; $V_{en} = H$		44	60	mA
	Current (pin 20)	$V_i = H$; $I_O = 0$; $V_{en} = H$		16	22	mA
		V _{en} = L		16	24	mA
V _{IL}	Input Low Voltage (pin 2, 9, 12, 19)		- 0.3		1.5	V
VIH	Input High Voltage (pin 2, 9,	$V_{SS} \le 7 V$	2.3		V _{SS}	V
	12, 19)	V _{SS} > 7 V	2.3		7	V
Ι _{ΙL}	Low Voltage Input Current (pin 2, 9, 12, 19)	V _{IL} = 1.5 V			- 10	μΑ
I _{IH}	High Voltage Input Current (pin 2, 9, 12, 19)	$2.3~V \leq V_{IH} \leq V_{SS} - 0.6~V$		30	100	μΑ
$V_{en L}$	Enable Low Voltage (pin 1, 11)		- 0.3		1.5	V
V _{en H}	Enable High Voltage	$V_{SS} \leq 7 V$	2.3		Vss	V
	(pin 1, 11)	V _{SS} > 7 V	2.3		7	V
I _{en L}	Low Voltage Enable Current (pin 1, 11)	V _{en L} = 1.5 V		- 30	- 100	μΑ
I _{en H}	High Voltage Enable Current (pin 1, 11)	$2.3 \text{ V} \leq \text{V}_{\text{en H}} \leq \text{V}_{\text{SS}} - 0.6 \text{ V}$			± 10	μΑ
V _{CE(sat)H}	Source Output Saturation Voltage (pins 3, 8, 13, 18)	$I_{\rm O} = -0.6 {\rm A}$		1.4	1.8	V
V _{CE(sat)L}	Sink Output Saturation Voltage (pins 3, 8, 13, 18)	I _O = + 0.6 A		1.2	1.8	V
VF	Clamp Diode Forward Voltage	I _O = 600nA		1.3		V
tr	Rise Time (*)	0.1 to 0.9 V _O		250		ns
t _f	Fall Time (*)	0.9 to 0.1 V ₀		250		ns
t _{on}	Turn-on Delay (*)	0.5 V _i to 0.5 V _O		750		ns
t _{off}	Turn-off Delay (*)	0.5 V _i to 0.5 V ₀		200		ns

ELECTRICAL CHARACTERISTICS (for each channel, $V_S = 24$ V, $V_{SS} = 5$ V, $T_{amb} = 25$ °C, unless otherwise specified)

(*) See fig. 1.

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TRUTH TABLE (one channel)

Input	Enable (*)	Output
Н	Н	Н
L	Н	L
Н	L	Z
L	L	Z

Z = High output impedance

(*) Relative to the considered channel



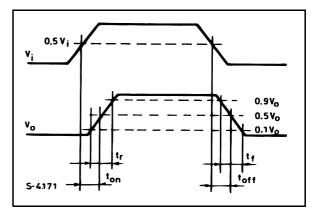
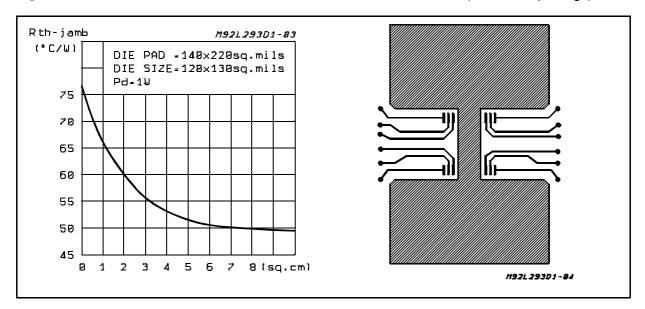
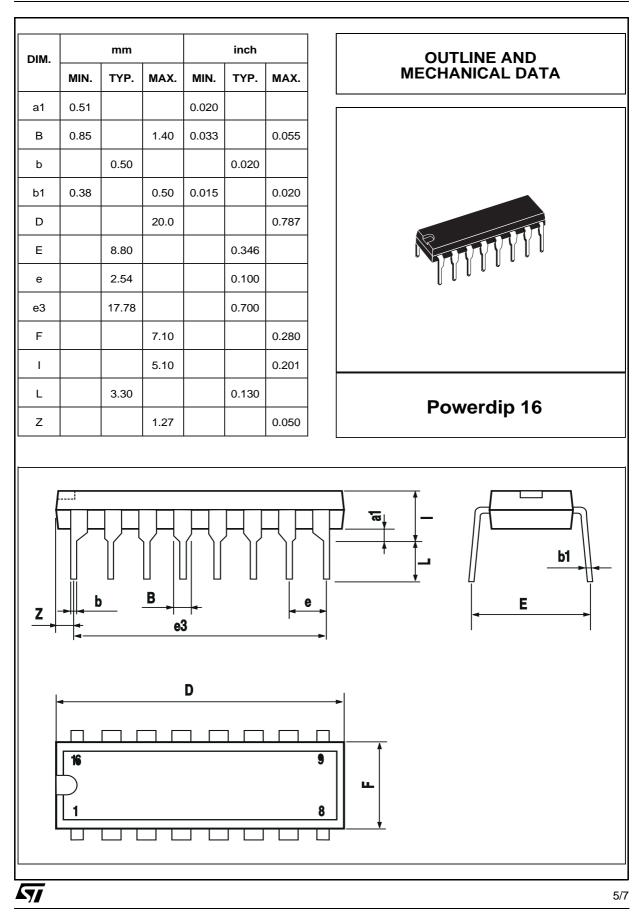


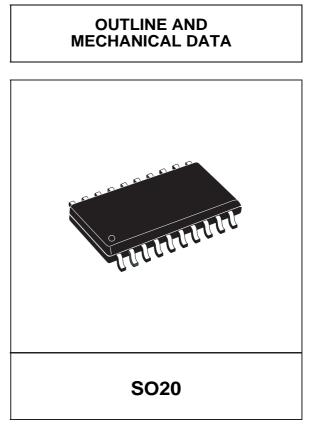
Figure 2: Junction to ambient thermal resistance vs. area on board heatsink (SO12+4+4 package)

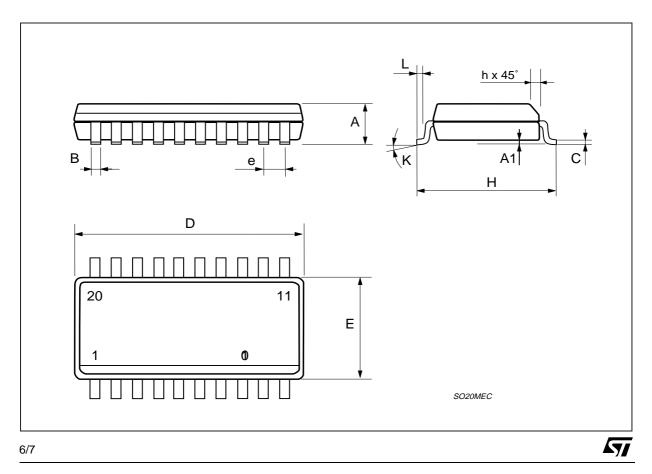




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DIM.	mm			inch			
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А	2.35		2.65	0.093		0.104	
A1	0.1		0.3	0.004		0.012	
В	0.33		0.51	0.013		0.020	
С	0.23		0.32	0.009		0.013	
D	12.6		13	0.496		0.512	
Е	7.4		7.6	0.291		0.299	
е		1.27			0.050		
н	10		10.65	0.394		0.419	
h	0.25		0.75	0.010		0.030	
L	0.4		1.27	0.016		0.050	
к	0° (min.)8° (max.)						





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